

# UN5111/5112/5113/5114/5115/5116/5117/5118/5119/5110/ 511D/511E/511F/511H/511L/511M/511N/511T/511V/511Z

## Silicon PNP epitaxial planer transistor

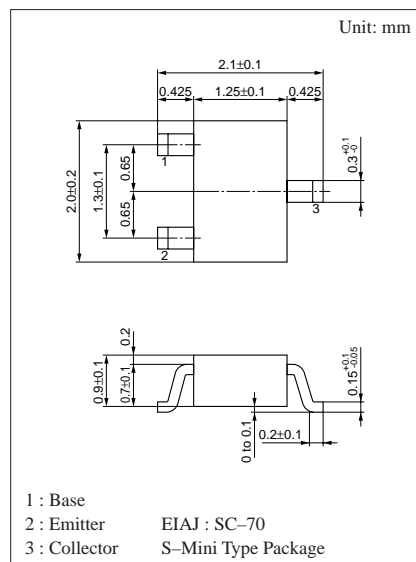
For digital circuits

### Features

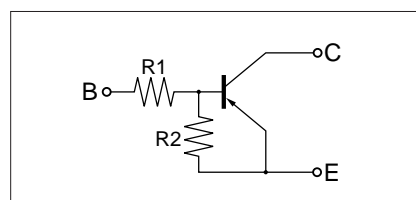
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- S-Mini type package, allowing automatic insertion through tape packing and magazine packing.

### Resistance by Part Number

	Marking Symbol	(R <sub>1</sub> )	(R <sub>2</sub> )
• UN5111	6A	10kΩ	10kΩ
• UN5112	6B	22kΩ	22kΩ
• UN5113	6C	47kΩ	47kΩ
• UN5114	6D	10kΩ	47kΩ
• UN5115	6E	10kΩ	—
• UN5116	6F	4.7kΩ	—
• UN5117	6H	22kΩ	—
• UN5118	6I	0.51Ω	5.1kΩ
• UN5119	6K	1kΩ	10kΩ
• UN5110	6L	47kΩ	—
• UN511D	6M	47kΩ	10kΩ
• UN511E	6N	47kΩ	22kΩ
• UN511F	6O	4.7kΩ	10kΩ
• UN511H	6P	2.2kΩ	10kΩ
• UN511L	6Q	4.7kΩ	4.7kΩ
• UN511M	EI	2.2kΩ	47kΩ
• UN511N	EW	4.7kΩ	47kΩ
• UN511T	EY	22kΩ	47kΩ
• UN511V	FC	2.2kΩ	2.2kΩ
• UN511Z	FE	4.7kΩ	22kΩ



### Internal Connection



### Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	-50	V
Collector to emitter voltage	V <sub>CEO</sub>	-50	V
Collector current	I <sub>C</sub>	-100	mA
Total power dissipation	P <sub>T</sub>	150	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

UN5111/5112/5113/5114/5115/5116/5117/5118/5119/5110/  
Transistors with built-in Resistor 511D/511E/511F/511H/511L/511M/511N/511T/511V/511Z

■ Electrical Characteristics (Ta=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current		I <sub>CBO</sub>	V <sub>CB</sub> = −50V, I <sub>E</sub> = 0			− 0.1	μA
		I <sub>CEO</sub>	V <sub>CE</sub> = −50V, I <sub>B</sub> = 0			− 0.5	μA
Emitter cutoff current	UN5111	I <sub>EBO</sub>	V <sub>EB</sub> = −6V, I <sub>C</sub> = 0			− 0.5	mA
	UN5112/5114/511E/511D/511M/511N/511T					− 0.2	
	UN5113					− 0.1	
	UN5115/5116/5117/5110					− 0.01	
	UN511F/511H					−1.0	
	UN5119					−1.5	
	UN5118/511L/511V					−2.0	
	UN511Z					− 0.4	
Collector to base voltage		V <sub>CBO</sub>	I <sub>C</sub> = −10μA, I <sub>E</sub> = 0	−50			V
UN511N/511T/511V/511Z				−50			
Collector to emitter voltage		V <sub>CEO</sub>	I <sub>C</sub> = −2mA, I <sub>B</sub> = 0	−50			V
UN511N/511T				−50			
Forward current transfer ratio	UN5111	h <sub>FE</sub>	V <sub>CE</sub> = −10V, I <sub>C</sub> = −5mA	35			
	UN5112/511E			60			
	UN5113/5114/511M			80			
	UN5115*/5116*/5117*/5110*			160		460	
	UN511F/511D/5119/511H			30			
	UN5118/511L			20			
	UN511N/511T			80		400	
	UN511V			6		20	
	UN511Z			60		200	
Collector to emitter saturation voltage		V <sub>CE(sat)</sub>	I <sub>C</sub> = −10mA, I <sub>B</sub> = − 0.3mA			− 0.25	V
UN511V			I <sub>C</sub> = −10mA, I <sub>B</sub> = −1.5mA			− 0.25	
Output voltage high level		V <sub>OH</sub>	V <sub>CC</sub> = −5V, V <sub>B</sub> = − 0.5V, R <sub>L</sub> = 1kΩ	−4.9			V
Output voltage low level		V <sub>OL</sub>	V <sub>CC</sub> = −5V, V <sub>B</sub> = −2.5V, R <sub>L</sub> = 1kΩ			− 0.2	V
			V <sub>CC</sub> = −5V, V <sub>B</sub> = −3.5V, R <sub>L</sub> = 1kΩ			− 0.2	
			V <sub>CC</sub> = −5V, V <sub>B</sub> = −10V, R <sub>L</sub> = 1kΩ			− 0.2	
			V <sub>CC</sub> = −5V, V <sub>B</sub> = −6V, R <sub>L</sub> = 1kΩ			− 0.2	
Transition frequency		f <sub>T</sub>	V <sub>CB</sub> = −10V, I <sub>E</sub> = 1mA, f = 200MHz		80		MHz
UN511Z			V <sub>CB</sub> = −10V, I <sub>E</sub> = 1mA, f = 200MHz		150		
Input resistance	UN5111/5114/5115	R <sub>i</sub>		(−30%)	10	( +30%)	kΩ
	UN5112/5117/511T				22		
	UN5113/5110/511D/511E				47		
	UN5116/511F/511L/511N/511Z				4.7		
	UN5118				0.51		
	UN5119				1		
	UN511H/511M/511V				2.2		

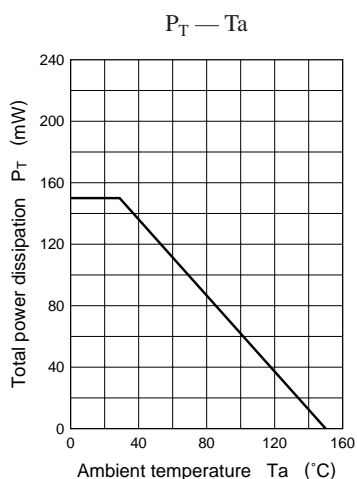
\*  $h_{FE}$  rank classification (UN5115/5116/5117/5110)

Rank	Q	R	S
$h_{FE}$	160 to 260	210 to 340	290 to 460

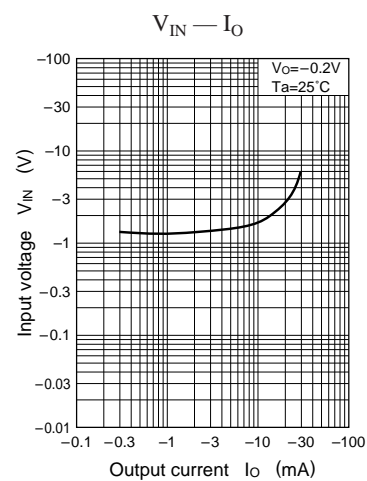
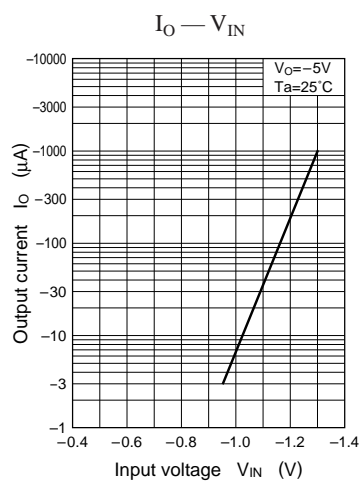
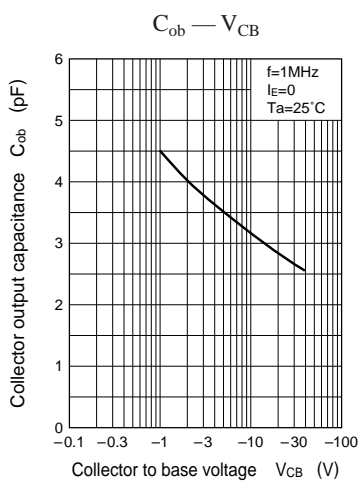
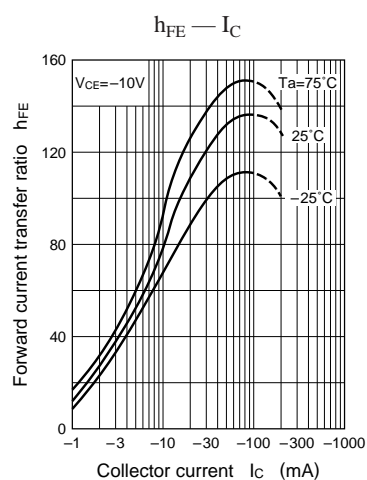
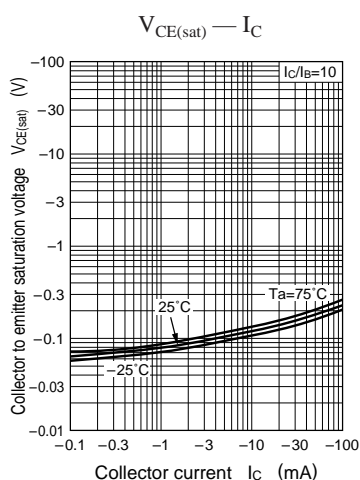
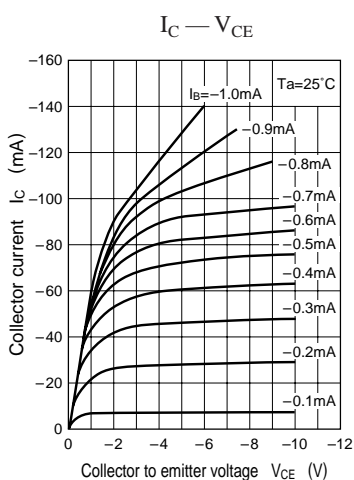
■ Electrical Characteristics (continued) (Ta=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Resis- tance ratio	UN5111/5112/5113/511L	$R_1/R_2$		0.8	1.0	1.2	
	UN5114			0.17	0.21	0.25	
	UN5118/5119			0.08	0.1	0.12	
	UN511D				4.7		
	UN511E				2.14		
	UN511F/511T				0.47		
	UN511H			0.17	0.22	0.27	
	UN511M				0.047		
	UN511N				0.1		
	UN511V				1.0		
	UN511Z				0.21		

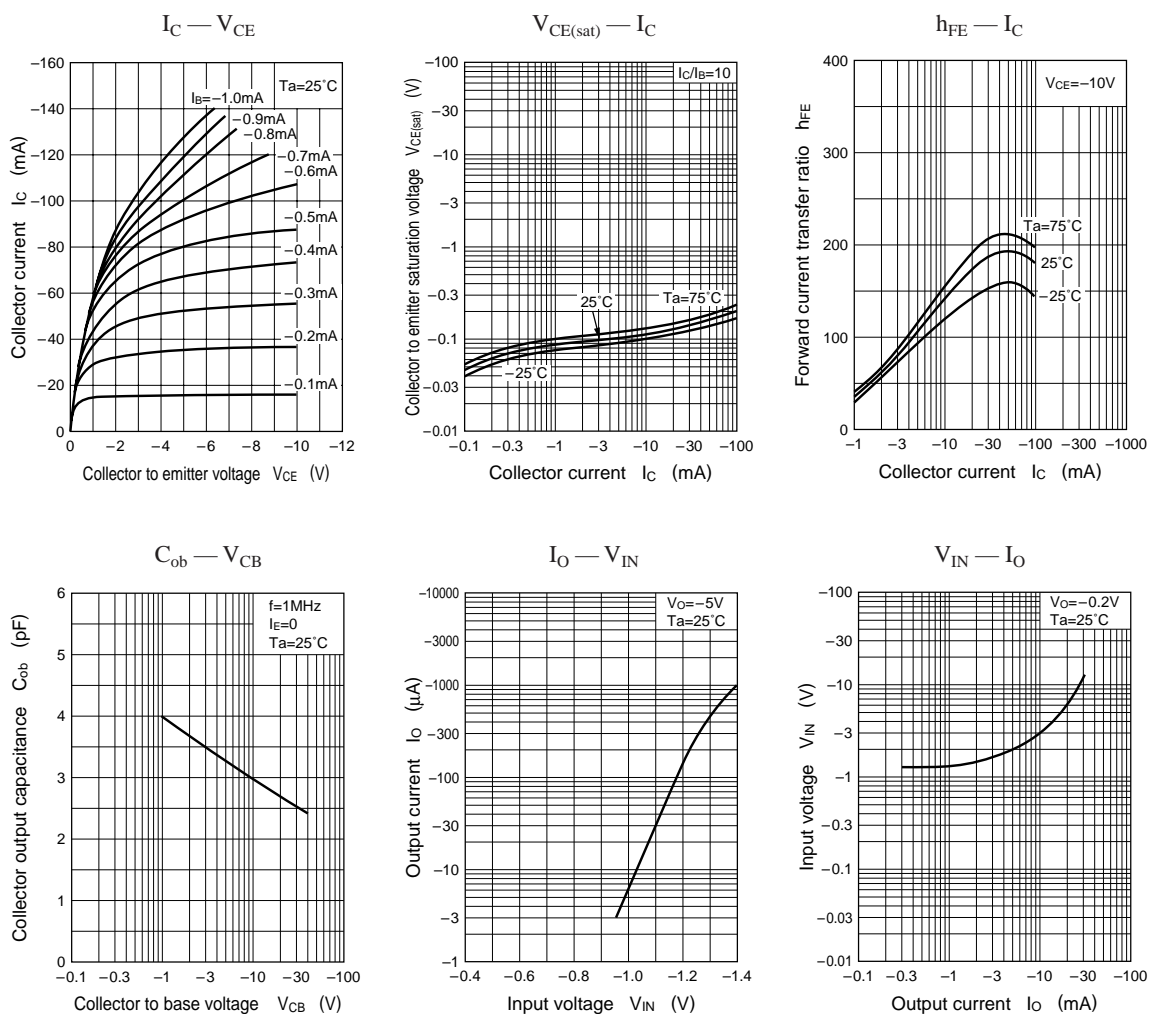
Common characteristics chart



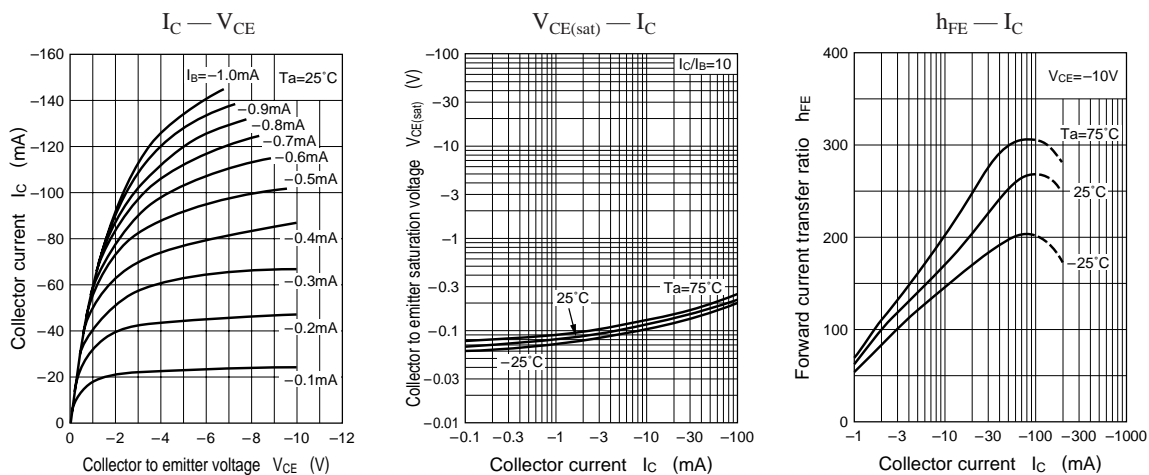
Characteristics charts of UN5111

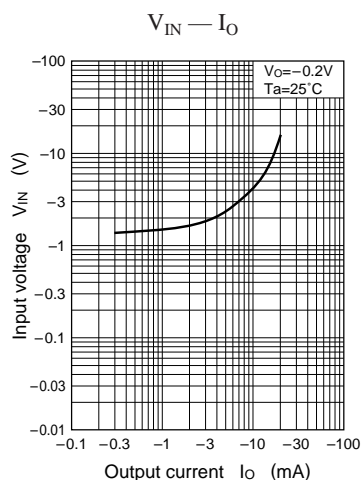
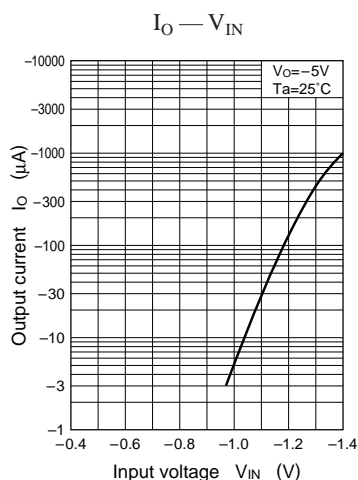
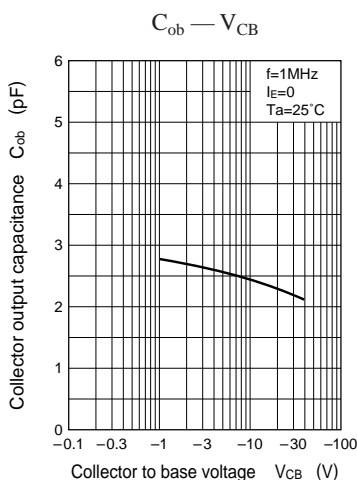


Characteristics charts of UN5112

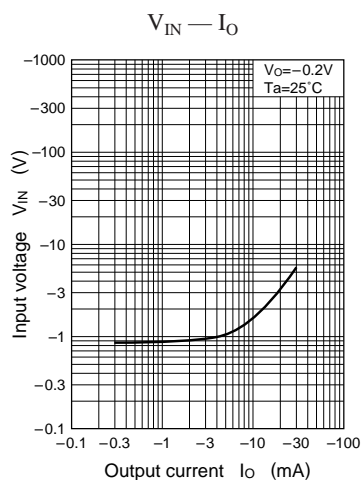
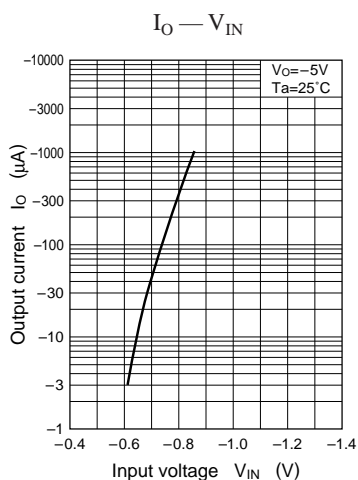
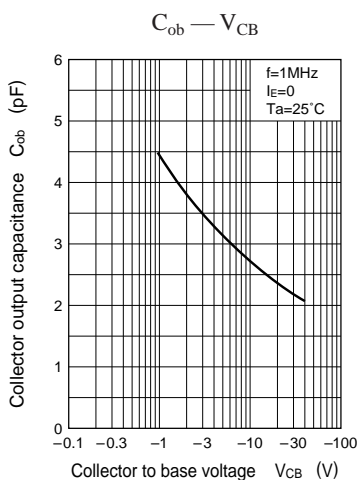
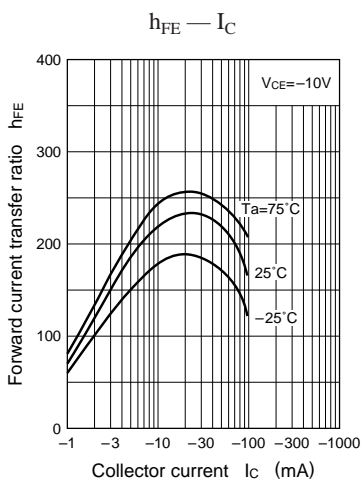
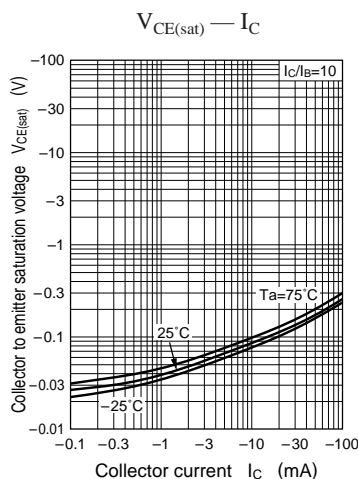
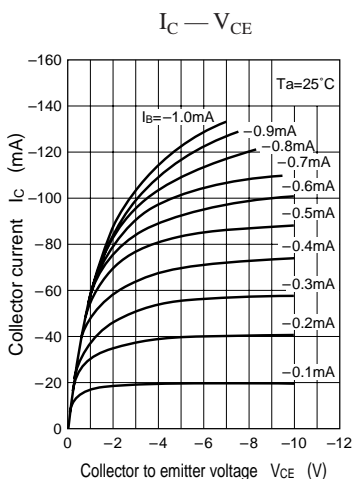


Characteristics charts of UN5113

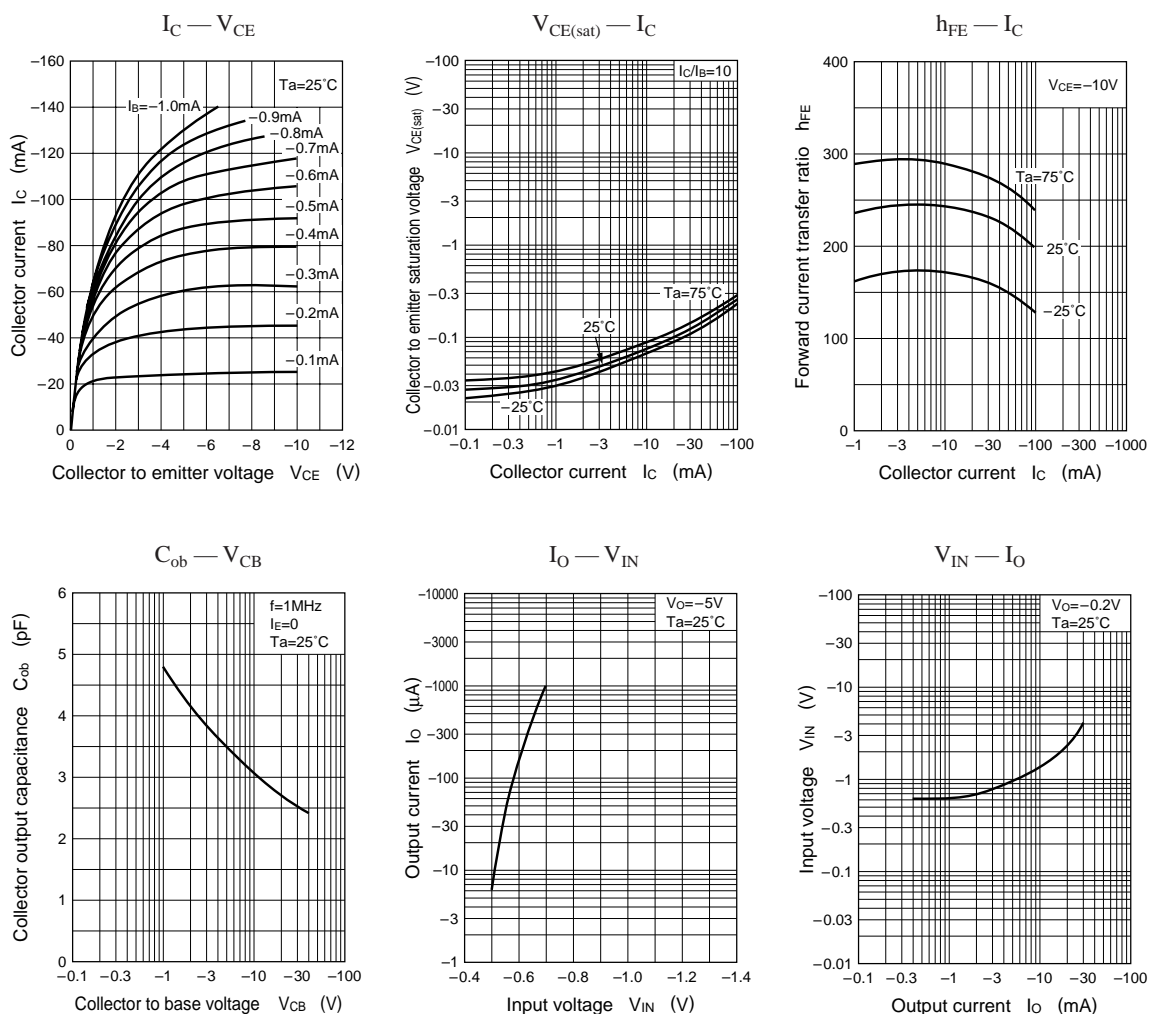




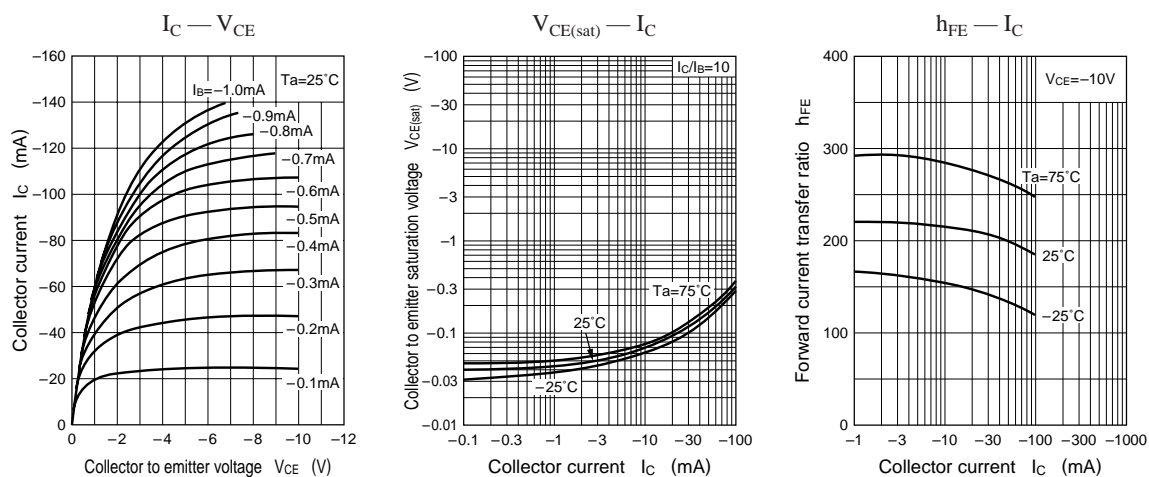
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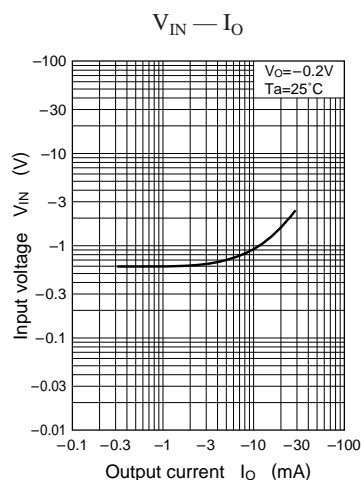
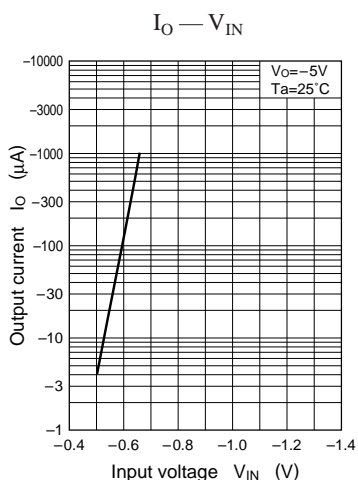
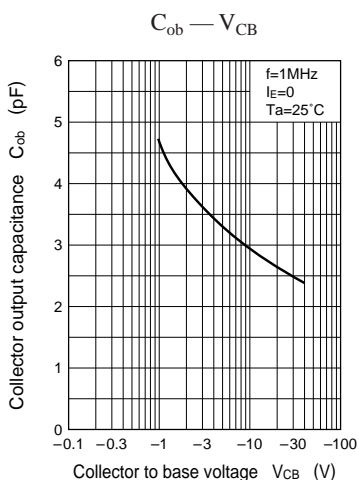


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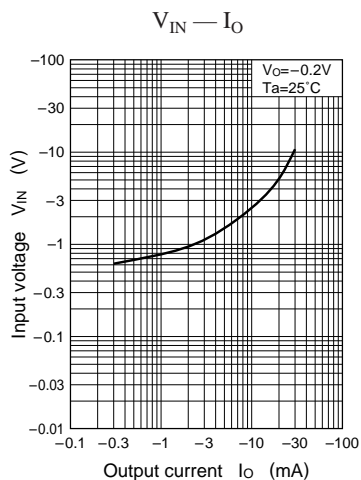
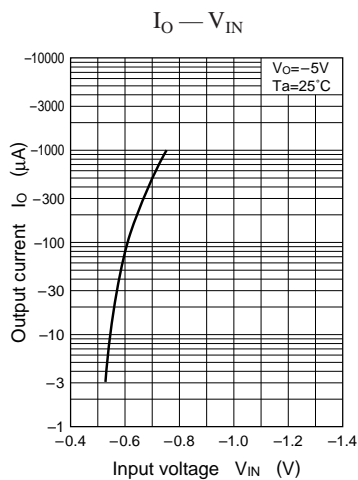
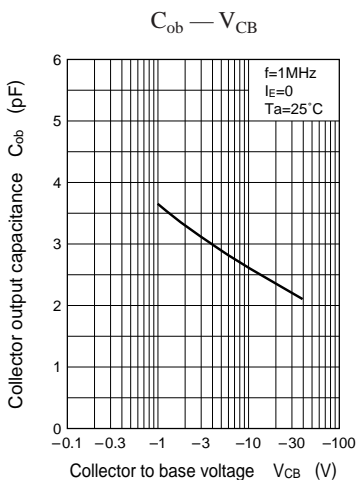
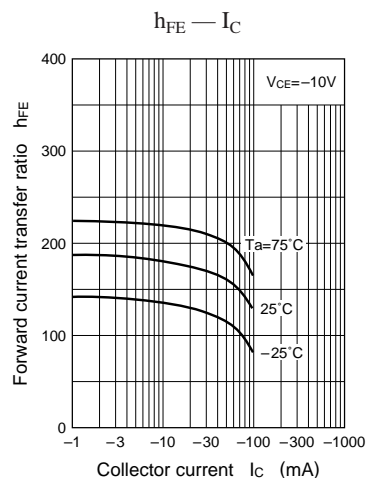
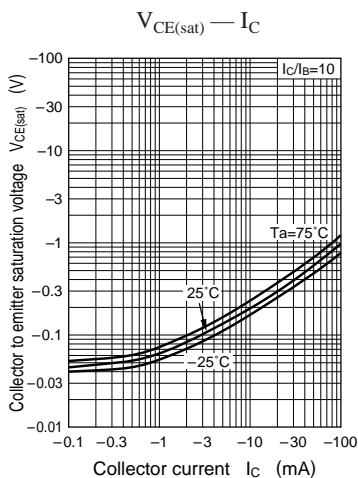
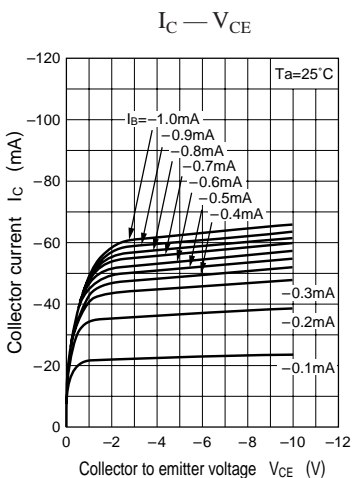


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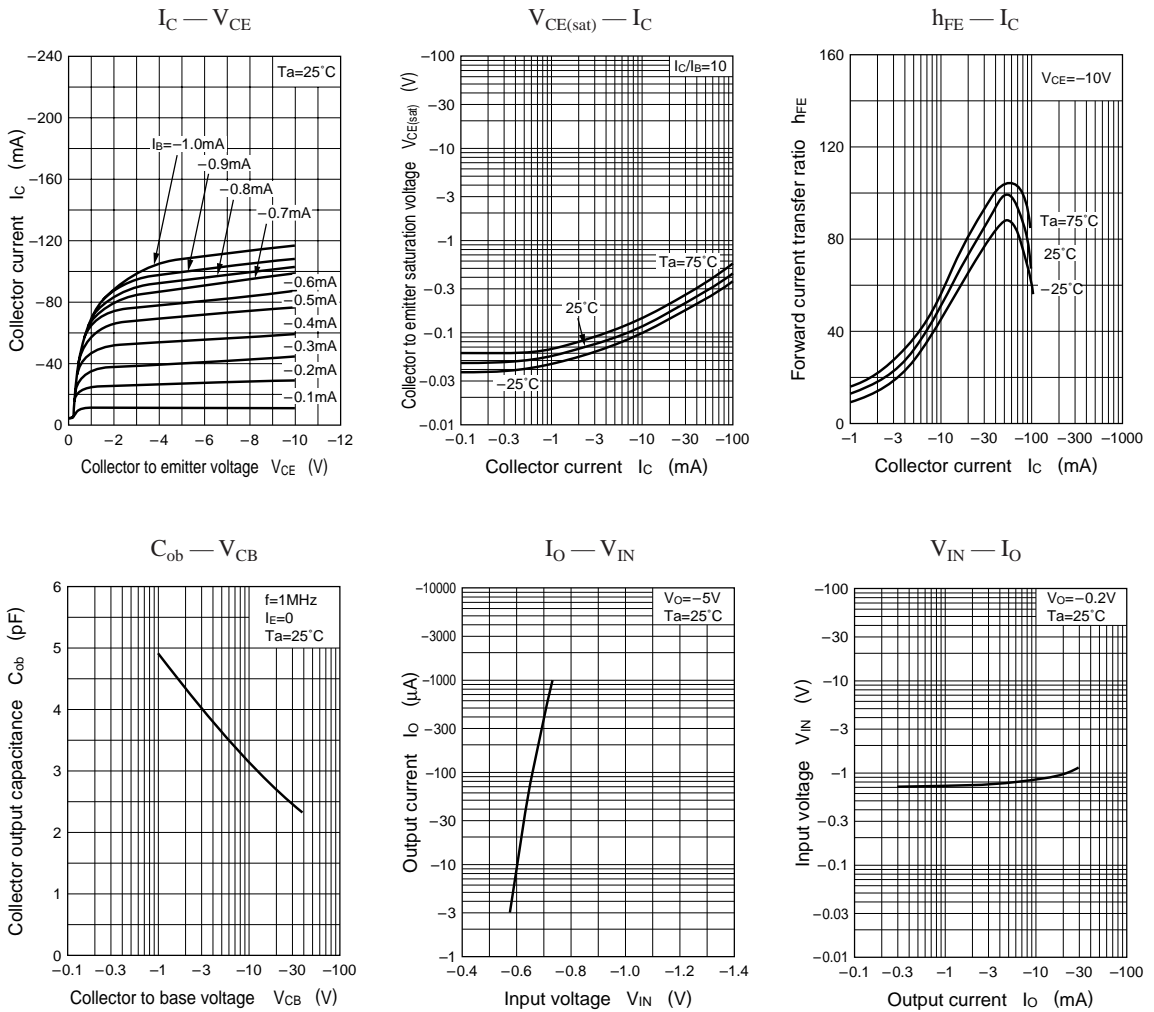


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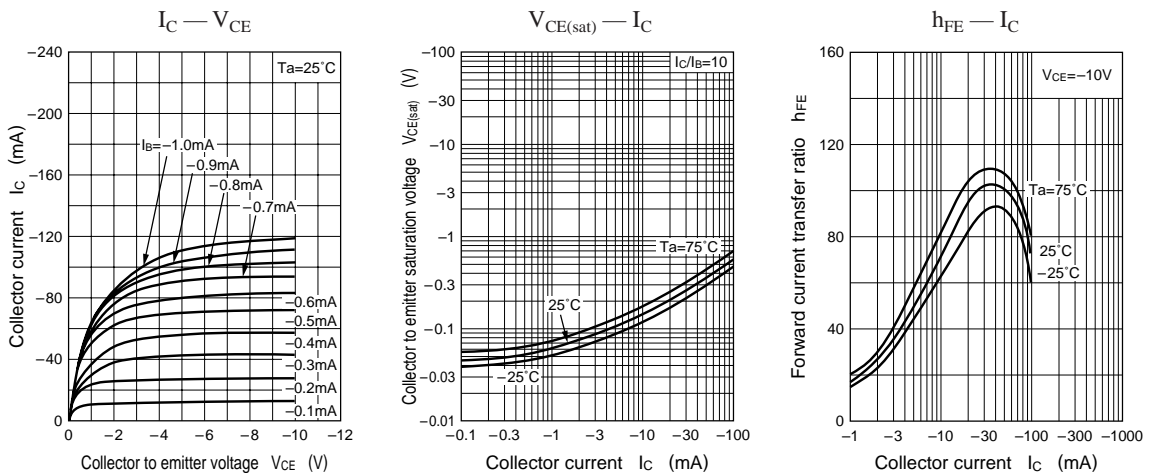


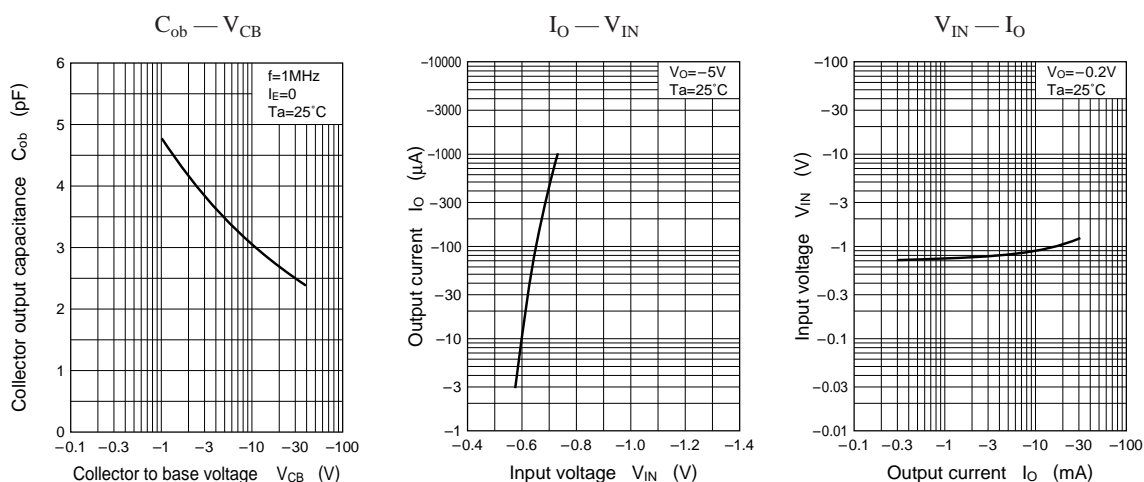


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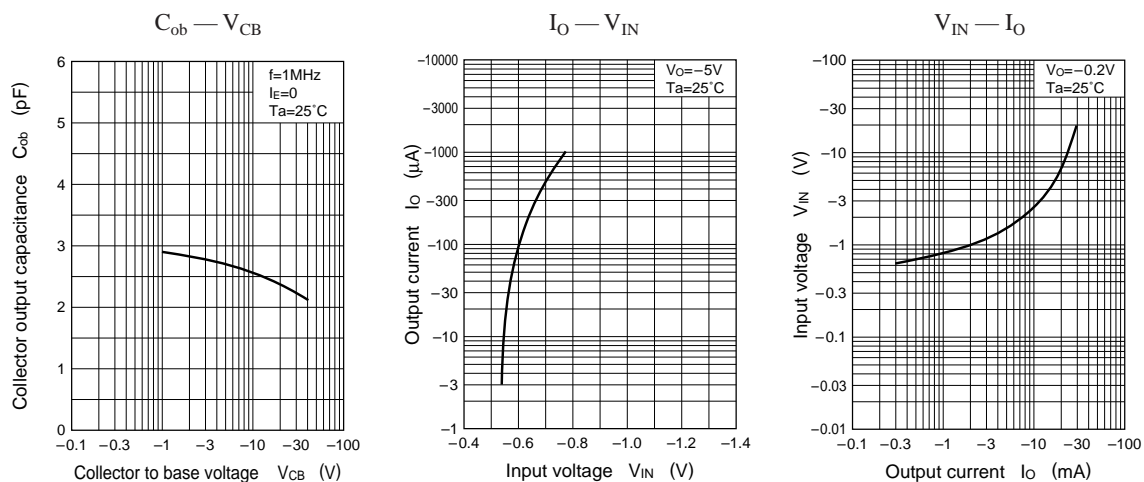
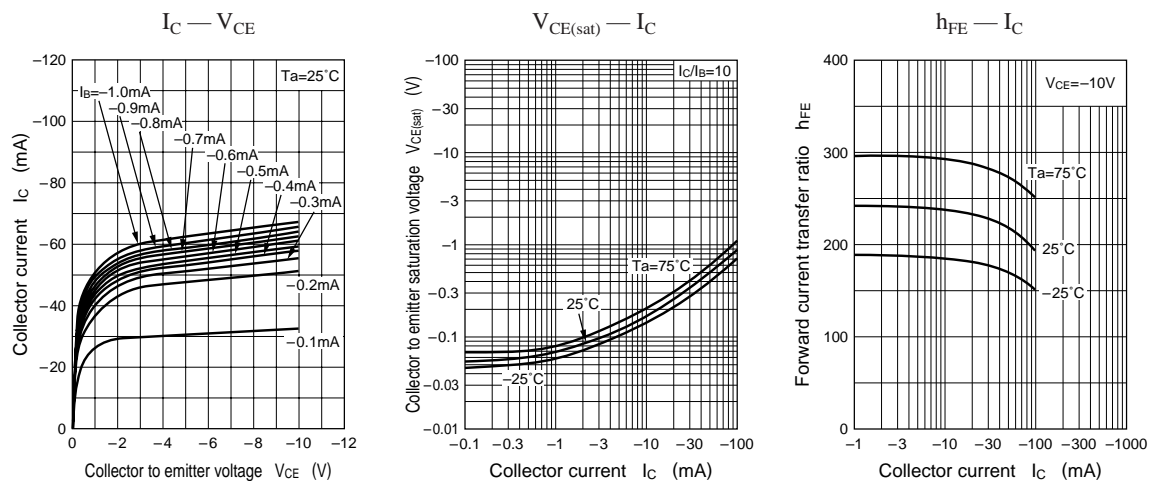


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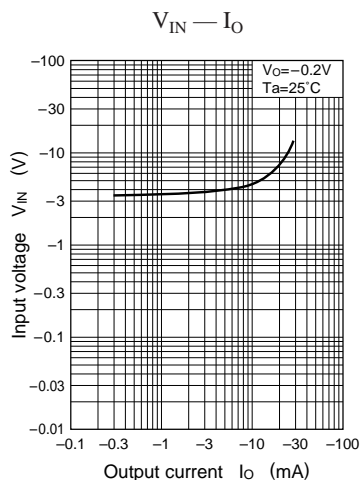
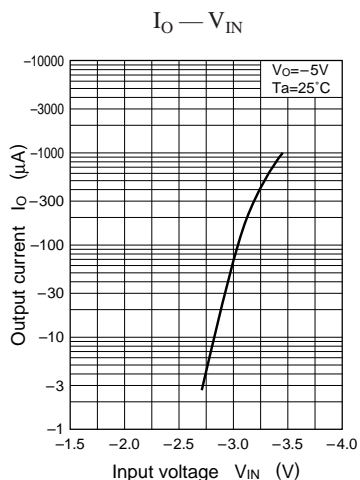
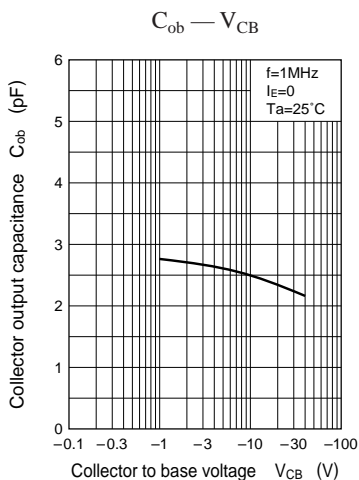
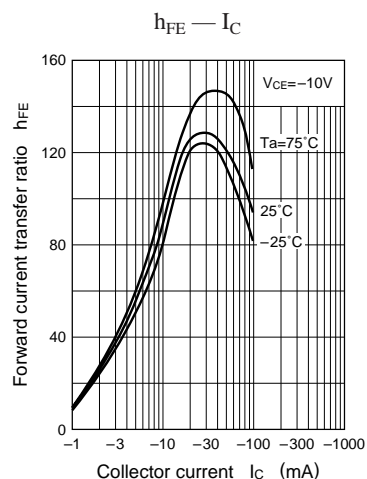
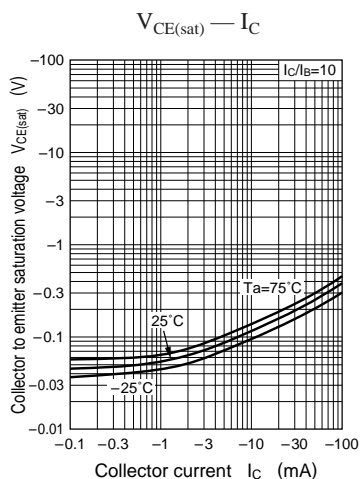
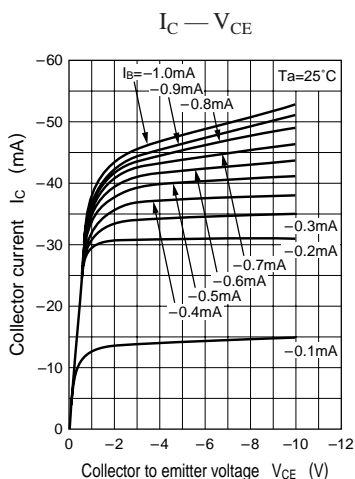




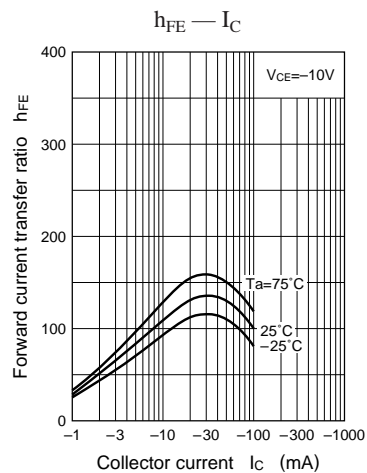
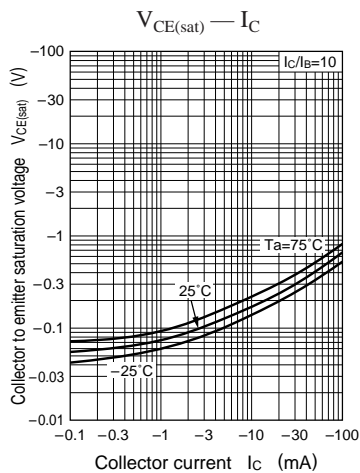
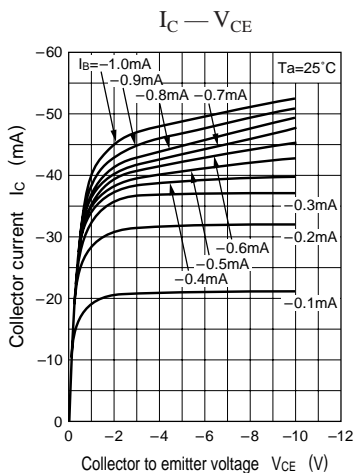
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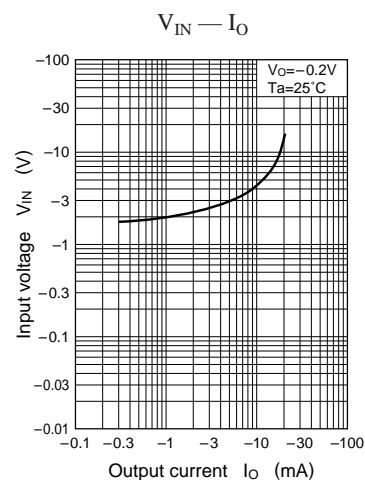
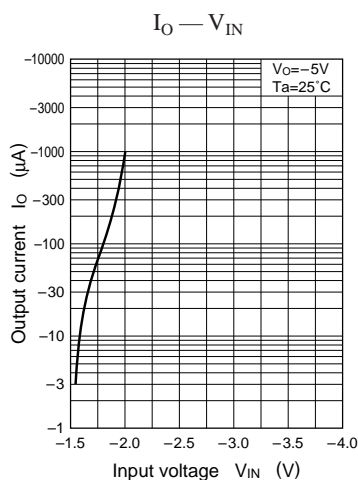
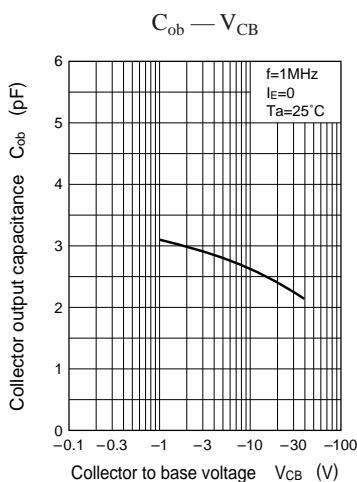


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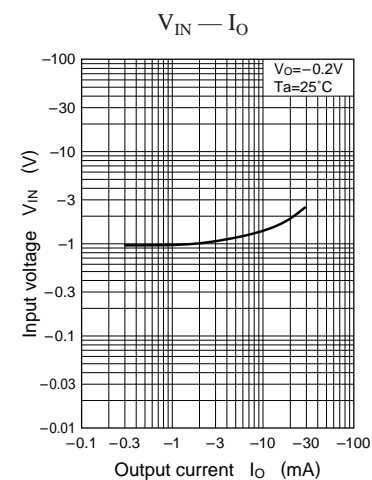
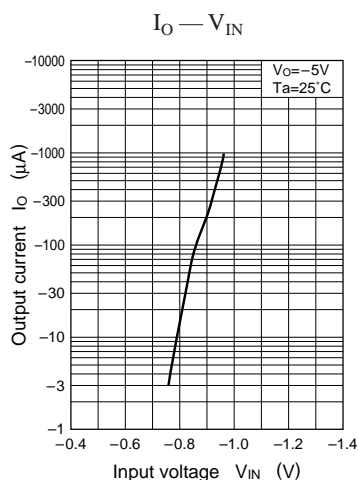
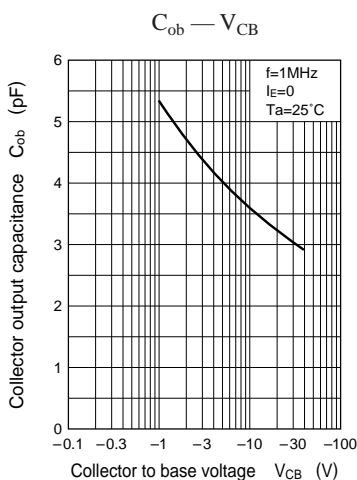
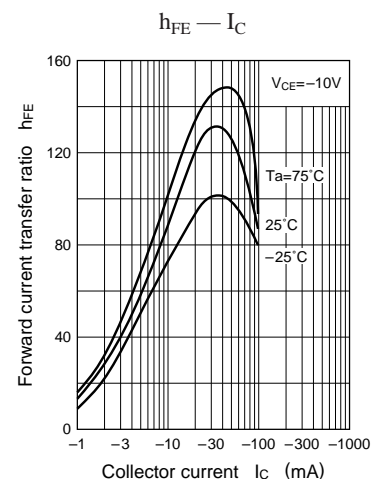
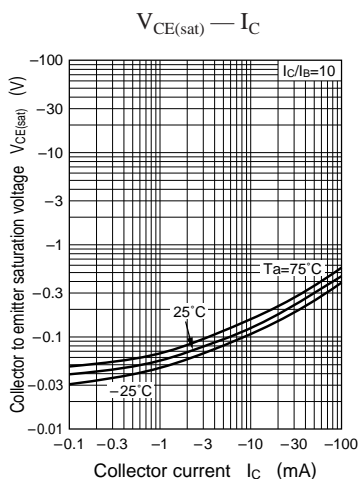
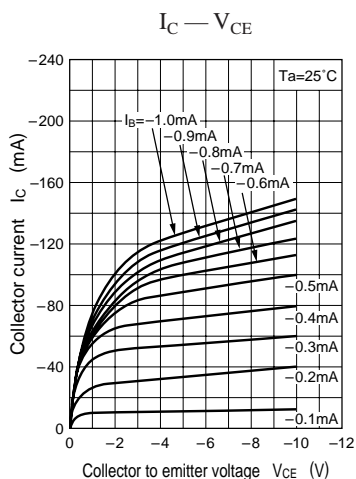


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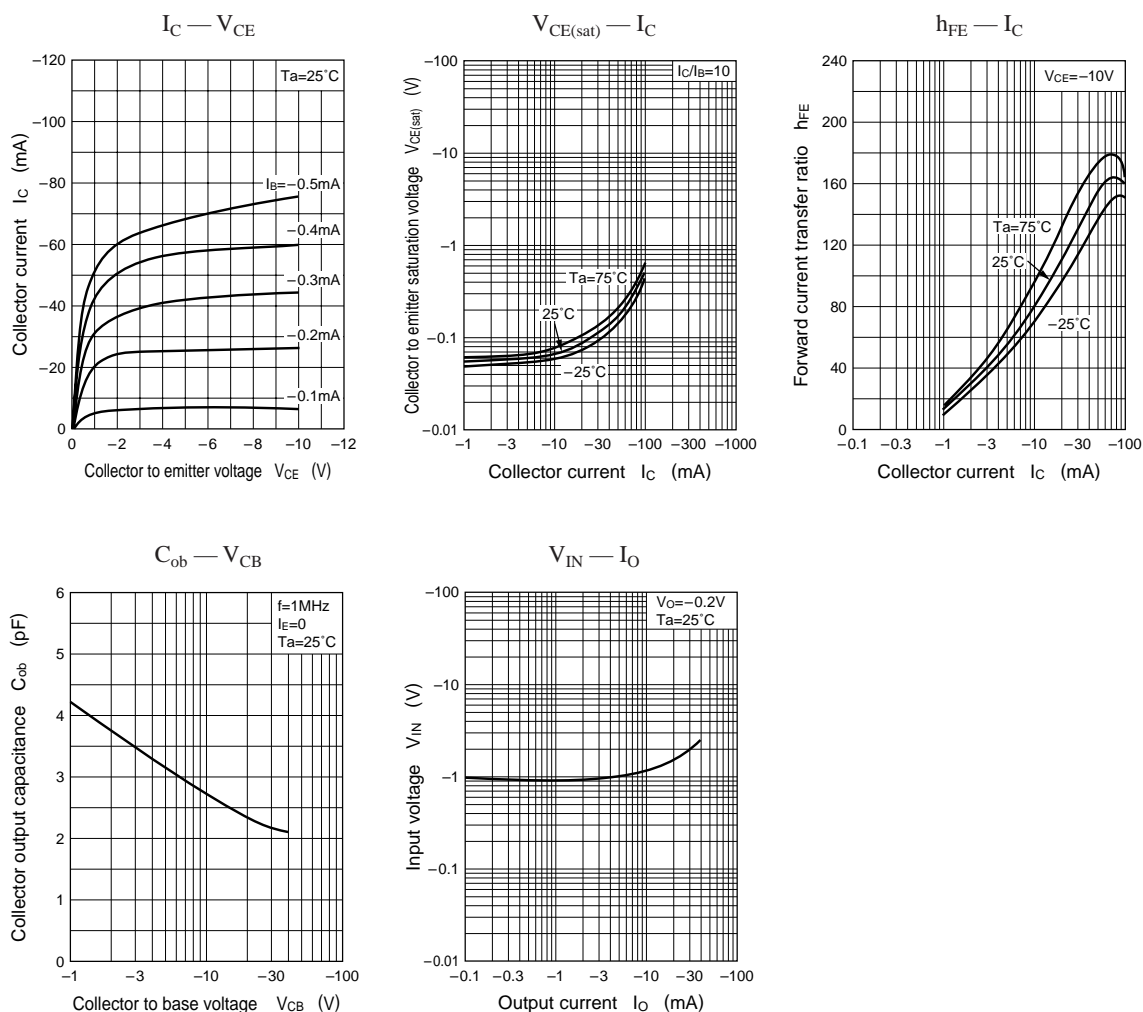




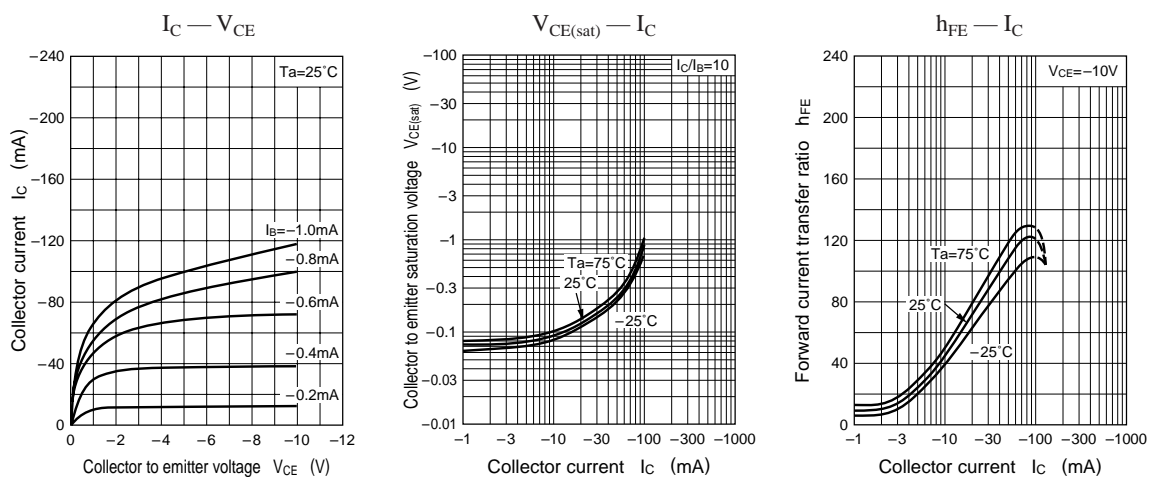
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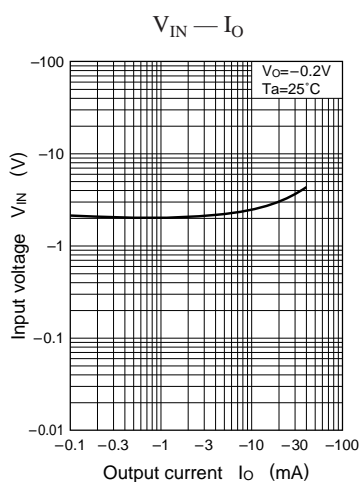
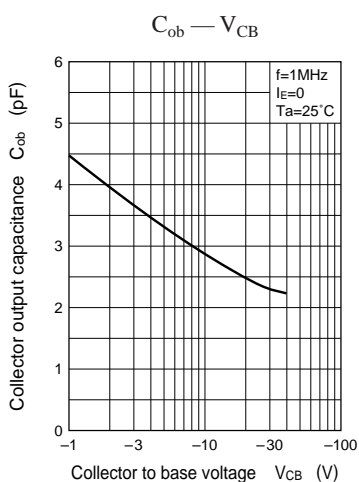


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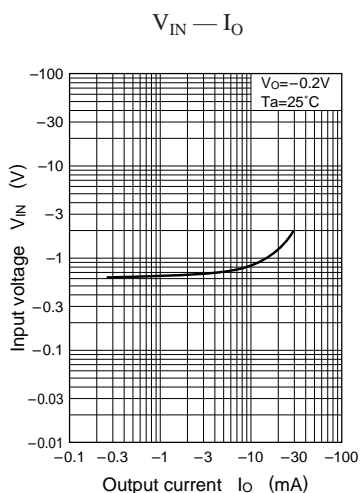
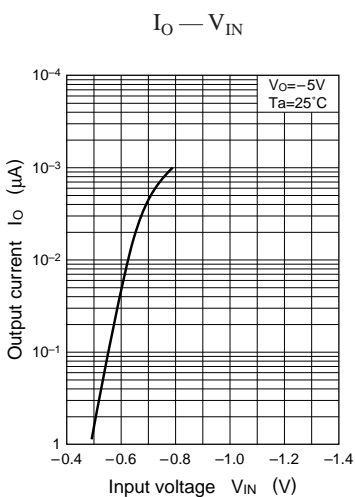
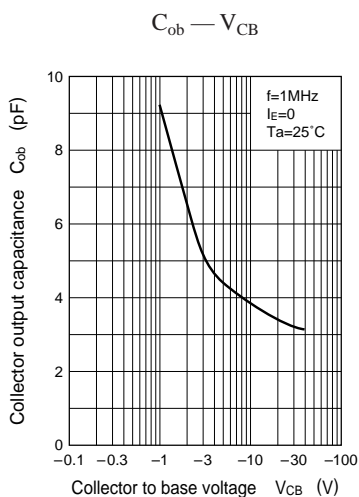
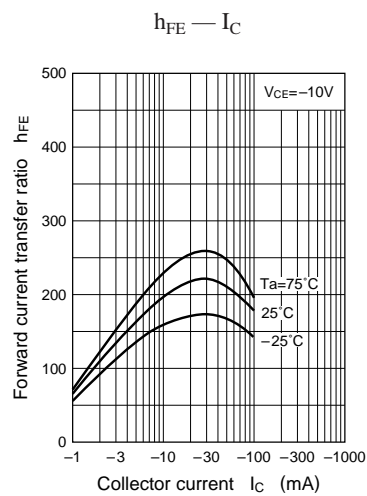
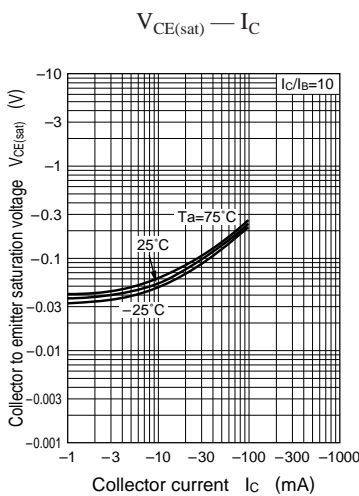
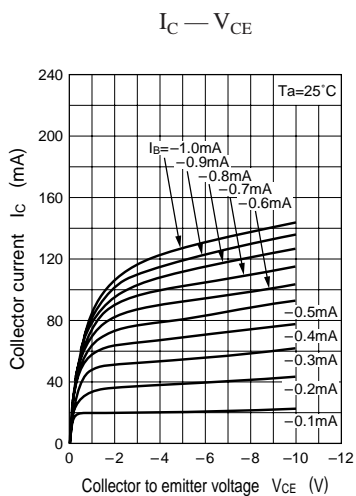


Characteristics charts of UN511L

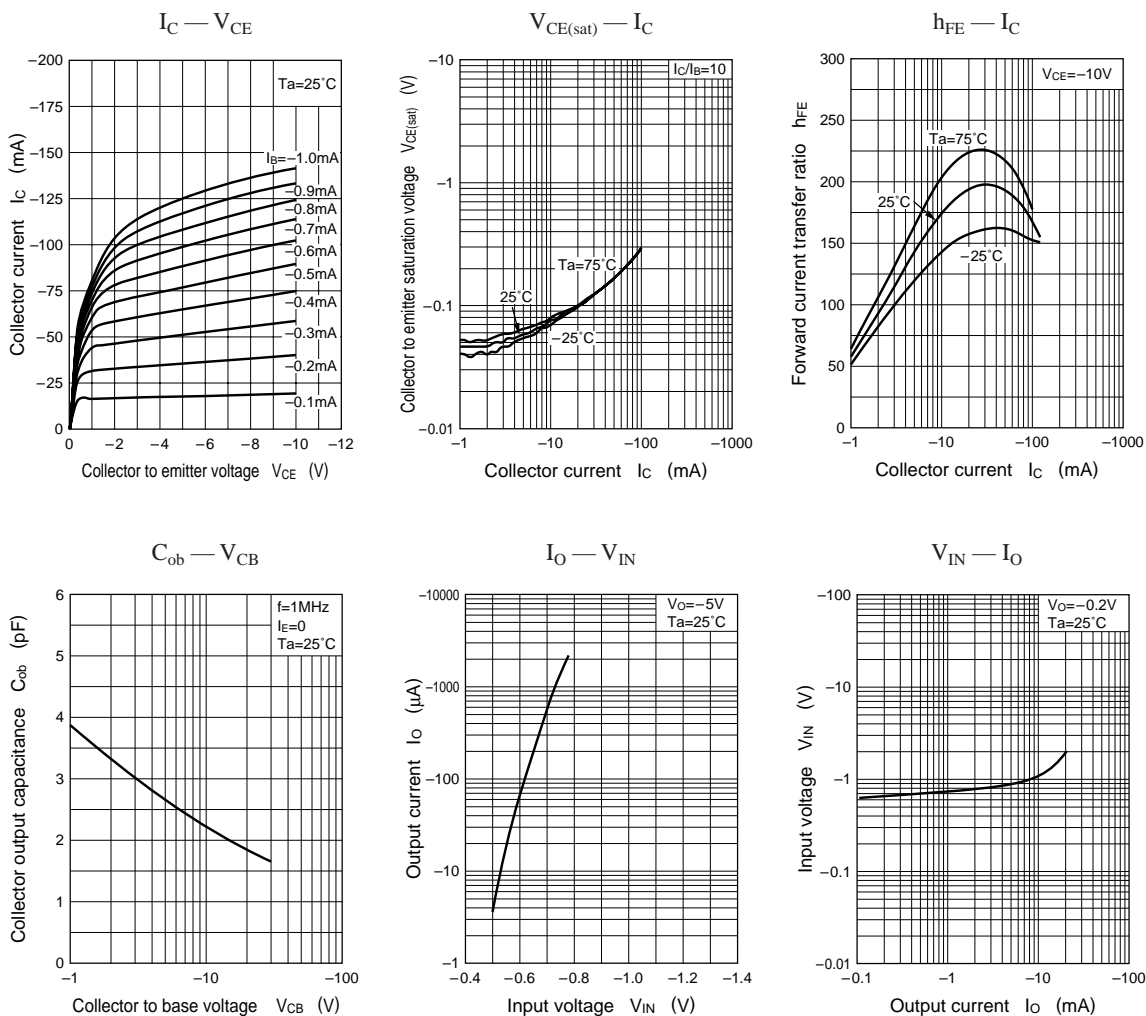




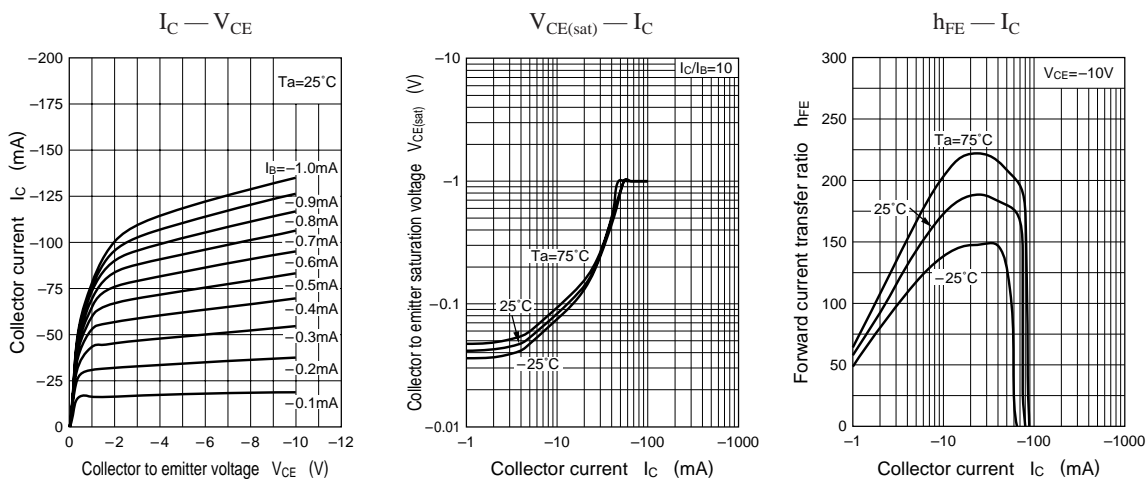
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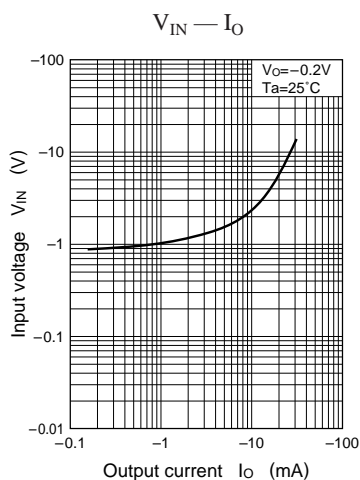
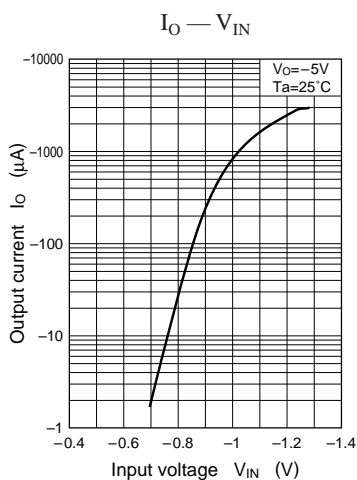


Characteristics charts of UN511N

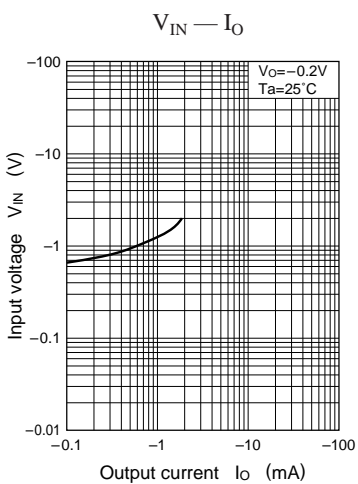
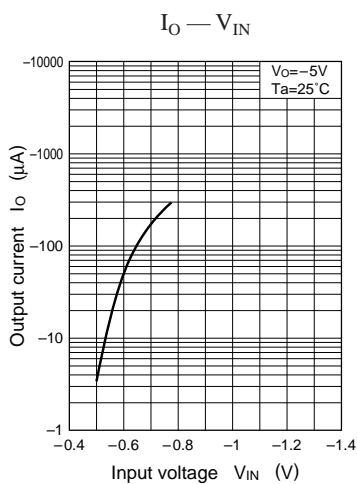
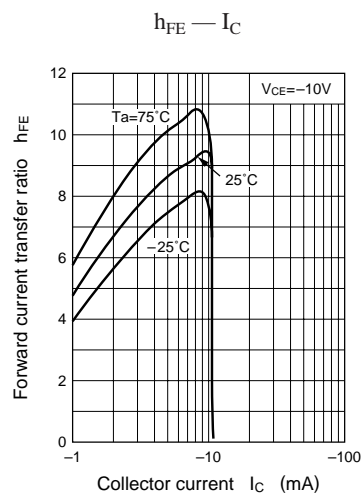
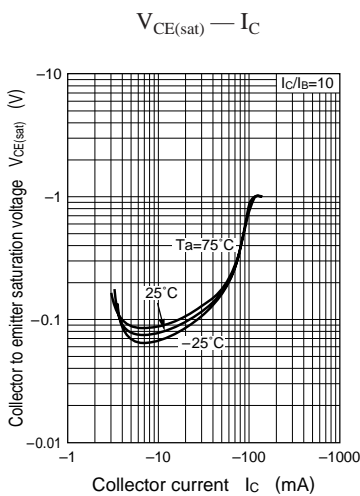
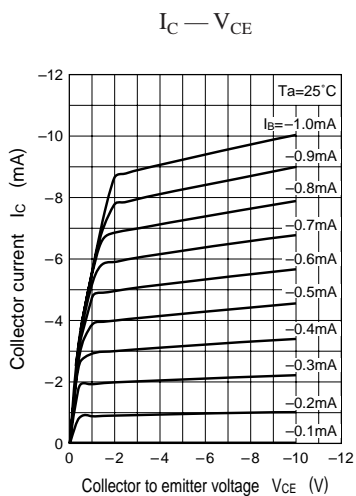


Characteristics charts of UN511T





Characteristics charts of UN511V





Characteristics charts of UN511Z

